

MvpLED™ SL-V-B28AD

High Power BLUE LED

BLUE LED

Introduction

The advantages of the patented and proprietary MvpLED™ design especially in Thermal management, and Optical efficacy, are realized in light quality, lifetime, color consistency, reliability and overall efficiency of the luminaire. Available in UV, Violet, Blue and Green, SemiLEDs high efficiency chips bring real benefits to any lamp or luminaire manufacturer.

Copper alloy, used in SemiLEDs MvpLED™ chips, is a better conductor of heat than any other material on the market used in the fabrication of LEDs. This is a major advantage for any lamp or luminaire manufacturer. No matter how good a thermal design is if the contact material to the junction is a poor conductor then the cooling effects of the heat-sink are significantly reduced.

Using a proprietary surface texturing technique, SemiLEDs LEDs maximize light extraction and efficiency. Coupled with the lack of Sapphire and a 90% efficient Reflective Layer, SemiLEDs chips exhibit an almost perfect Lambertian radiation pattern.

SemiLEDs' patented and unique process consumes no Sapphire, significantly reducing the Carbon footprint. The lack of a Sapphire base also removes a thermal management bottleneck while providing the most environmentally friendly LED on the market.

RoHS and REACH Compliant

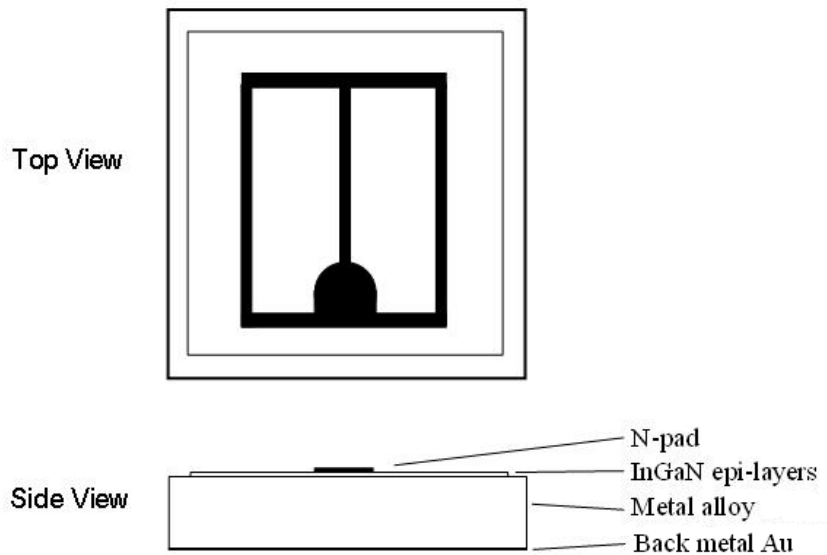
Feature

Metal alloy device-----	Low cost high thermal conductivity
Thickness 95 μm -----	Consolidated metal alloy
P-N junction high at 90 μm -----	Silver epoxy die attachment compatible
One pad structure-----	Low package cost
Nearly Perfect Lambertian emission pattern -----	Ideal for white light design
Patterned surface -----	Maximum light extraction

Applications

LCD backlight
 Digital Camera Flash light
 High Power LED
 Automotive lighting
 Signalling
 Signage
 Miniature Light Engine

Chip Mechanical Diagram



Mechanical Specifications

P-N junction area	640 μm X 640 μm	$\pm 20 \mu\text{m}$
Base area	720 μm X 720 μm	$\pm 50 \mu\text{m}$
Chip thickness	95 μm	$\pm 15 \mu\text{m}$
Bond pad size	120 μm	$\pm 10 \mu\text{m}$
Bond pad thickness	2.5 μm	$\pm 0.5 \mu\text{m}$
Junction height	90 μm	$\pm 15 \mu\text{m}$

Optical and Electrical Characteristics at 350mA, Ta at 25°C

Parameter	Symbol	Min	Typ	Max	Remark
Forward voltage:	Vf		3.5	3.8	Volt
Spectra half width	$\Delta\lambda$		20	40	nm
Reverse current	Ir			2 μ A	Vr= 5 Volt

Measured by SemiLEDs on bare chip

Absolute Maximum Ratings, Ta at 25°C

Forward Current (DC)	350 mA
Peak Forward Current (1/10 duty cycle @ 1KHz)	500 mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature	-40°C to +110°C
Storage Temperature	-40°C to +110°C
Temperature during packaging (reflow)	280°C < 10 sec

Maximum ratings are strongly package dependent and may differ between different packaged devices. The values given were collected by SemiLEDs' in-house package.

BIN Table (Output Power at 350mA, Ta at 25°C)

Wd Range(nm)	240-290mW	290-350mW	350-400mW
450-452.5	AD	AE	AF
452.5-455	BD	BE	BF
455-457.5	CD	CE	CF
457.5-460	DD	DE	DF
460-462.5	ED	EE	EF
462.5-465	FD	FE	FF
465-467.5	GD	GE	
467.5-470	HD	HE	
470-472.5	ID	IE	
472.5-475	JD	JE	

Performance Diagram

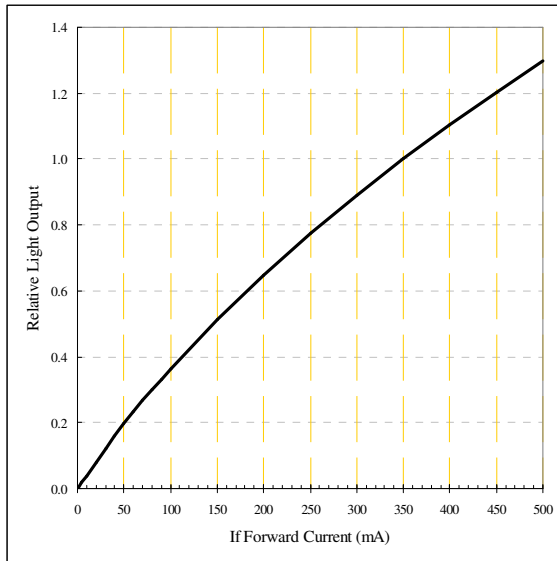


Fig-1 Relative Output Power vs. Forward Current.

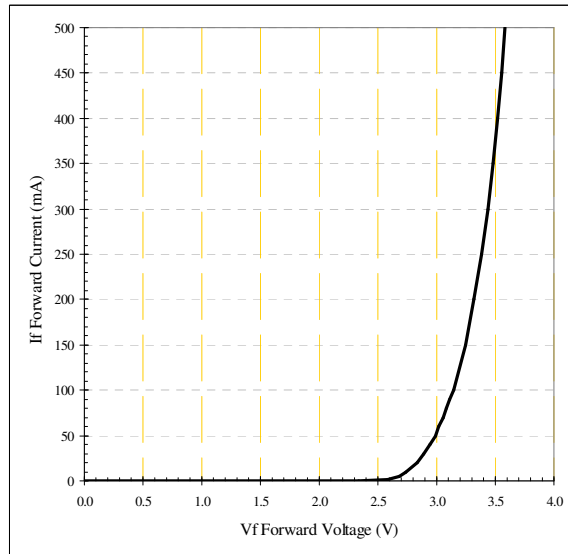


Fig-2 Forward Current vs. Forward Voltage.

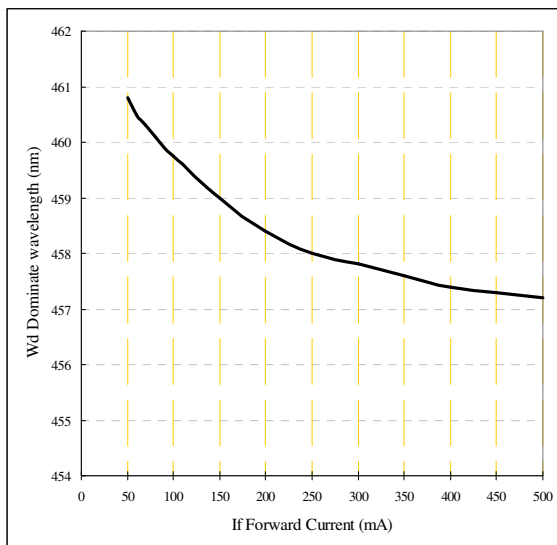


Fig-3 Forward Dominate Wavelength vs. Forward Current.

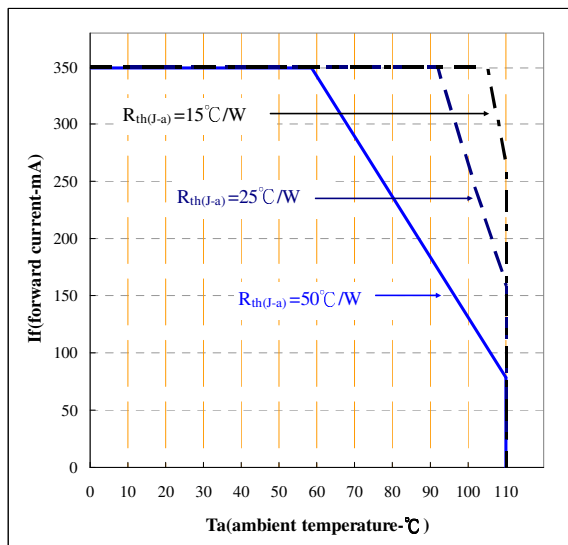


Fig-4 Maximum Driving Forward DC Current vs. Ambient Temperature.

Note:

- Minimum and maximum value refers to the limits and set up of SemiLEDs' testers. All other measurement data are defined as long-term production mean values and are only given for information.
- A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system. Life support devices or systems are intended (i) to be implanted in the human body, or (ii) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered. Components used as a critical component must be approved in writing by SemiLEDs.

About Us

SemiLEDs is a US based manufacturer of ultra-high bright LED chips with state of the art fabrication facilities in Hsinchu Science Park, Taiwan. SemiLEDs specializes in the development and manufacturing of metal alloy vertical LED chips in blue (white), green and UV using our patented and proprietary MvpLED™ technology. This unique design allows for higher performance and longer lumen maintenance. SemiLEDs new high power I-core MvpLEDs™ can deliver over 120lm/W. In December 2008 The World Economic Forum recognized SemiLEDs innovations with the 2009 Technology Pioneer Award.



www.semileds.com

AMERICAS

SemiLEDs Corporation
999 Main Street, Suite 1010
Boise, ID 83702
United States

Tel +1.208.389.7426
Fax +1.208.389.7515
sales@semileds.com

ASIA PACIFIC

3F, No. 11, KeJung Rd.
Hsinchu Science Park
Chu-Nan 350, Miao-Li
Taiwan

Tel: +886-37-586788
Fax: +886-37-582688
sales@semileds.com